AMENDMENT UNDER 37 C.F.R. § 1.116 Attorney Docket No.: Q93262

Appln. No.: 10/571,054

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the

application:

LISTING OF CLAIMS:

1.-16. (Canceled).

17. (Currently amended): A dye-sensitized solar cell comprising a transparent

electrode substrate, a working electrode having an oxide semiconductive porous film formed on

the transparent electrode substrate which is made of oxide semiconductive fine particles and

having a photo-sensitizing dye absorbed thereon, and a counter electrode provided opposing the

working electrode, and an electrolyte layer comprising the electrolyte composition according to

elaim 1-which is provided between the working electrode and the counter electrode, and wherein

the electrolyte composition comprises an ionic liquid and a halogen-based redox pair, wherein

the ionic liquid includes dicyanoamide anions.

18. (Original): The dye-sensitized solar cell according to claim 17 wherein the

transparent electrode substrate comprises a conductive layer made of a conductive material on a

transparent substrate.

19. (Original): The dye-sensitized solar cell according to claim 18 wherein the

transparent substrate includes glass, a transparent plastic substrate, and a polished plate of a

ceramic.

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20. (Original): The dye-sensitized solar cell according to claim 18 wherein the conductive layer includes a transparent oxide semiconductor selected from the group consisting of tin-doped indium oxide (ITO), tin oxide (SnO₂), fluorine-doped tin oxide (FTO), and mixtures thereof.

- 21. (Original): The dye-sensitized solar cell according to claim 18 wherein the conductive layer has a thickness of between about $0.05~\mu m$ and $2.0~\mu m$.
- 22. (Original): The dye-sensitized solar cell according to claim 17 wherein the oxide semiconductor porous film is a porous thin layer with a thickness between about 0.5 and 50 μm containing as a main component oxide semiconductor fine particles which include titanium oxide (TiO₂), tin oxide (SnO₂), tungsten oxide (WO₃), zinc oxide (ZnO), niobium oxide (Nb₂O₅), and mixtures thereof, where said oxide semiconductor fine particles have an average particle diameter between 1 nm to 1000 nm.
- 23. (Original): The dye-sensitized solar cell according to claim 17 measuring photoelectric conversion efficiency greater than 4.5%.